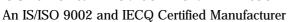


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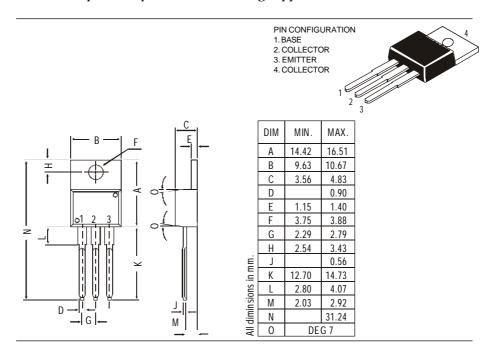




TO-220 Plastic Package

BD241, BD241A, BD241B, BD241C BD242, BD242A, BD242B, BD242C

BD241, 241A, 241B, 241C NPN PLASTIC POWER TRANSISTORS BD242, 242A, 242B, 242C PNP PLASTIC POWER TRANSISTORS General Purpose Amplifier and Switching Applications



ABSOLUTE MAXIMUM RATINGS							
		241 241A 241B 241C					
		242	242A	242B	242C		
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max. 55	70	90	115	V	
Collector-emitter voltage (open base)	V_{CEO}	max. 45	60	<i>80</i>	100	V	
Collector current	I_C	max.	5.0			\boldsymbol{A}	
Total power dissipation up to $T_C = 25^{\circ}C$	P_{tot}	max.	4	0		W	
Junction temperature	T_{j}	max.	13	50		${}^{\circ}\!C$	
Collector-emitter saturation voltage	J						
$I_C = 3 A; I_B = 0.6 A$	V_{CEsat}	<i>max.</i> 1.2		.2		V	
D.C. current gain							
$I_C = 1 A$; $V_{CE} = 4 V$	h_{FE}	min.	25				
RATINGS (at T_A =25°C unless otherwise s	specified)						
Limiting values		241	241A	241B	241C		
		242	242A	242B	242C		
Collector-emitter voltage ($V_{BE} = 0$)	$V_{C\!E\!S}$	max. 55	70	90	115	V	
Collector-emitter voltage (open base)	V_{CEO}	max. 45	60	<i>80</i>	100	V	
Collector-emitter voltage ($R_{BE} = 100\Omega$)	V_{CER}	max. 55	70	90	115	V	

BD241, BD241A, BD241B, BD241C BD242, BD242A, BD242B, BD242C

Emitter-base voltage (open collector)	V_{EBO}	max.		5.0			V
Collector current	I_C	max.	<i>max.</i> 3.0				\boldsymbol{A}
Collector current (Peak value)	I_C	max.		5.	0		\boldsymbol{A}
Base current	ΙΒ	max.		1.0			\boldsymbol{A}
Total power dissipation upto $T_C=25$ °C	P_{tot}	max.		4	0		W
Derate above 25°C	tot	max.		0.32			$W^{\circ}C$
Junction temperature	T_{j}	max.		<i>150</i>			${}^{\!$
Storage temperature	T_{stg}			-65	${\mathscr C}$		
THERMAL RESISTANCE							
From junction to case	R_{thj-c}			3.125			${}^{\circ}\!CW$
From junction to ambient	R _{th j-a}			62.5			°CW
	rui j–a			02	.0		011
CHARACTERISTICS							
$T_{amb} = 25$ °C unless otherwise specified			041	0414	0 4 1 D	0410	
				241A			
C-ll-t			242	242A	Z4ZB	Z4ZC	
Collector cutoff current	7		0.0	0.0			4
$I_B = 0$; $V_{CE} = 30 \text{ V}$	I_{CEO}	max.		0.3	-	_	mA
$I_B = 0$; $V_{CE} = 60 \text{ V}$	I_{CEO}	max.	-	-	0.3	0.3	mA
$V_{BE} = 0; V_{CE} = V_{CEO}$	I_{CES}	max.		0.	Z		mA
Emitter cut-off current							
$I_C = 0$; $V_{EB} = 5 V$	I_{EBO}	max.		1.0			mA
Breakdown voltages							
$I_C = 30 \text{ mA}; I_B = 0$	V _{CEO(sus)}			60	80	100	V
$I_C = 1 \text{ mA}; V_{BE} = 0$	V_{CES}	min.	55	70	90	115	V
$I_E = 1 \text{ mA}; I_C = 0$	V_{EBO}	min.		5.	0		V
Saturation voltage							
$I_C = 3 A; I_B = 0.6 A$	V_{CEsat}^*	max.		1.2			V
Base emitter on voltage							
IC = 3 A; $VCE = 4 V$	$V_{BE(on)}^*$	max.		1.8			V
D.C. current gain							
$I_C = 1 A$; $V_{CE} = 4 V$	$h_{\!F\!E}^*$	min.		25			
$I_C = 3 A; V_{CE} = 4 V$	$h_{\!F\!E}^*$	min.		10			
Transition frequency							
$I_C = 0.5 \text{ A}$; $V_{CE} = 10 \text{ V}$; $f = 1 \text{ MHz}$	f _T (1)	min.		3			MHz
Small signal current gain							
$I_C = 0.5A; \ V_{CE} = 10V; \ f = 1 \ KHz$	h_{fe}	min.		2	0		
* Dulas tart mulas militar < 200 mm dute mu	-1- / 90/						

^{*} Pulse test: pulse width \leq 300 µs; duty cycle \leq 2% (1) $f_T = /h_{\rm fe}/\bullet f_{\rm test}$

Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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